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| Application Number     | Unassigned 10/540514 |
| Confirmation Number    | Unassigned           |
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| First Named Inventor   | Takenori OSADA       |
| Art Unit               | Unassigned           |
| Examiner Name          | Unassigned           |
| Attorney Docket Number | Q88664               |

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**U.S. PATENT DOCUMENTS**

| Examiner Initials* | Cite No. <sup>1</sup> | Document Number |                                      | Publication Date<br>MM-DD-YYYY | Name of Patentee or Applicant of Cited Document |
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|                    |                       | Country Code <sup>3</sup> | Number <sup>4</sup> | Kind Code <sup>5</sup><br>(if known) |                                |   |                          |
|                    |                       | JP                        | 06-163599           | A                                    | 06-10-1994                     | NEC Corporation                                 |                          |
|                    |                       | JP                        | 06-84959            | A                                    | 03-25-1994                     | Fujitsu Ltd.                                    |                          |
|                    |                       | JP                        | 2001-210819         | A                                    | 08-03-2001                     | Hitachi Cable, Ltd.                             |                          |
|                    |                       |                           |                     |                                      |                                |   |                          |
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**NON PATENT LITERATURE DOCUMENTS**

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|--------------------|-----------------------|--|--------------------------|
|                    |                       | Feng Zhao et al., "Hall and photoluminescence studies of effects of the thickness of an additional In <sub>0.3</sub> Ga <sub>0.75</sub> As layer in the center of In <sub>0.15</sub> Ga <sub>0.85</sub> As/Al <sub>0.25</sub> Ga <sub>0.75</sub> As/GaAs high electron mobility transistors", <i>Materials Science in Semiconductor Processing</i> , Vol. 5, February 2002, pp. 23-26. |                          |
|                    |                       | U. Strauße et al., "Carrier mobilities in graded In <sub>x</sub> Ga <sub>1-x</sub> As/Al <sub>0.2</sub> Ga <sub>0.8</sub> As quantum wells for high electron mobility transistors", <i>Journal of Applied Physics</i> , Vol. 80, No. 1, July 1, 1996, pp. 322-325.   |                          |
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